

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method of forming a thin film of magnesium boride on a silicon substrate, the method comprising:

introducing a substrate having a surface consisting essentially of silicon into a chamber;

physically generating vapor from at least one source of magnesium, which is within the chamber with the substrate; and

introducing at least one boron precursor to the chamber, which combines with the vapor from the at least one source of magnesium to form a thin film of superconductive magnesium boride on the surface consisting essentially of silicon of the substrate, wherein

the formed magnesium boride film is substantially free of magnesium-silicon contaminates between the surface consisting essentially of silicon and the magnesium boride film and

the pressure of the vapor is maintained within $\text{Log}(P) = -9549.5/T + 9.1$; and $\text{Log}(P) = -10142/T + 8.562$, where P represents pressure in units of Torr and T represents temperature in Kelvin.

2. (Original) The method of claim 1, comprising introducing a carrier gas to the chamber prior to, during, or after introducing the boron precursor.

3. (Original) The method of claim 2, wherein the carrier gas contains hydrogen and/or nitrogen.

4. (Original) The method of claim 1, comprising maintaining a pressure of about 0.1 to about 100 Torr in the chamber during formation of the magnesium boride film on the substrate.

5. (Original) The method of claim 1, comprising heating the at least one source of magnesium to a temperature of about 650 K to about 1300 K to physically generate vapor of the at least one source of magnesium.

6. (Original) The method of claim 1, comprising maintaining a distance of no less than several inches between the substrate and the at least one source of magnesium while physically generating vapor from the at least one source of magnesium.

7. (Original) The method of claim 1, wherein the boron precursor is boron trichloride, boron tribromide, diborane, trimethylboron, boron trifluoride, or any combination thereof.

8. (Original) The method of claim 1, comprising maintaining a pressure of about 0.1 Torr to about 30 Torr in the chamber during formation of the magnesium boride film on the substrate.

9. (Canceled)

10. (Original) The method of claim 1, comprising physically generating the vapor of the magnesium thermally, or by a pulsed laser.

11. (Original) The method of claim 1, comprising physically generating magnesium vapor from the at least one source of magnesium, and introducing a carrier gas to the chamber along with the boron precursor.

12. (Currently Amended) A method of forming a thin film of magnesium boride on a silicon substrate, the method comprising:

introducing a silicon substrate having a surface consisting essentially of silicon into a chamber;

physically generating magnesium vapor from a magnesium source by heating the magnesium source within the chamber;

introducing diborane to the chamber; and

forming a superconductive magnesium diboride thin film directly on the surface consisting essentially of silicon, wherein

the pressure of the magnesium vapor is maintained within about $\text{Log}(P) = -9549.5/T + 9.1$; and $\text{Log}(P) = -10142/T + 8.562$, where P represents pressure in units of Torr and T represents temperature in Kelvin (K).

13. (Canceled)

14. (Currently Amended) The method of claim ~~[[13]]~~ 12, comprising introducing a carrier gas to the chamber prior to, during, or after introducing the boron precursor.

15. (Previously Presented) The method of claim 14, comprising forming the magnesium diboride thin film directly on the surface consisting essentially of silicon of the substrate, wherein the formed magnesium boride film is substantially free of any non-magnesium diboride compound between the substrate and magnesium diboride film.

16. (Canceled)

17. (Previously Presented) A method of forming a thin film of magnesium boride on a silicon substrate, the method comprising:

introducing a silicon substrate into a chamber;

maintaining magnesium vapor at a magnesium partial pressure within the chamber between about $\text{Log}(P) = -9549.5/T + 9.1$ and about $\text{Log}(P) = -10142/T + 8.562$, P represents pressure in units of Torr and T represents temperature in Kelvin; and

introducing at least one boron precursor to the chamber to combine with the magnesium vapor to form a thin film of superconductive magnesium boride on the substrate.